

Abstract of the Disclosure

A method for forming of a capacitor wherein an etching barrier layer comprising a stacked structure of a 5 nitride film and a tantalum oxide film is disclosed. The method comprises the steps of: forming an etching barrier layer on an interlayer insulating film having a storage electrode contact plug therein, the etching barrier layer comprising a stacked structure of a nitride film and a 10 tantalum oxide film; forming an oxide film on the etching barrier layer; selectively etching the oxide film and the etching barrier layer to form an opening exposing the storage electrode contact plug; depositing a storage electrode layer on the bottom and the inner walls of the 15 opening; and removing the oxide film, whereby forming a storage electrode.